

FORM PTO-1449 U.S. Department of Commerce  
Patent and Trademark Office

Attorney Docket Number  
5308-168

Serial No.  
09/878,442

LIST OF DOCUMENTS CITED BY APPLICANT



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MAR 08 2004

Applicants: Das et al.

Filing Date: June 11, 2001

Group: 2815

U. S. PATENT DOCUMENTS

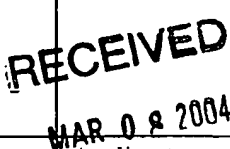
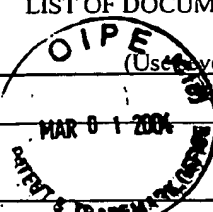
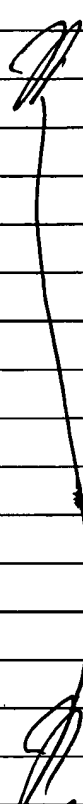


Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
<i>[Signature]</i>	1.	5,170,231	12/8/92	Fujii et al.	357	23.2	
	2.	5,885,870A	3/99	Maiti et al.	438	261	
	3.	5,939,763	8/17/99	Hao et al.	257	411	
	4.	5,960,289	9/28/99	Tsui et al.	438	257	
	5.	5,972,801	10/26/99	Lipkin et al.	438	770	
	6.	6,028,012	2/22/00	Wang	438	779	
	7.	6,048,766	4/11/00	Gardner et al.	438	257	
	8.	6,054,352	4/25/00	Ueno	438	268	
	9.	6,063,698	5/16/00	Tseng et al.	438	585	
	10.	6,096,607	8/1/00	Ueno	438	522	
	11.	6,117,735	9/12/00	Ueno	438	268	
	12.	6,136,728	10/24/00	Wang	438	773	
	13.	6,165,822	12/26/00	Okuno et al.	438	142	
	14.	6,190,973 B1	2/20/01	Berg et al.	438	275	
	15.	6,204,203	3/01	Narwanker et al.	438	785	
	16.	6,211,035	4/01	Moise et al.	438	396	
	17.	6,221,700	4/24/01	Okuno et al.	438	151	
	18.	6,239,463	05/29/01	Williams et al.	257	328	
	19.	6,297,172	10/2/01	Kashiwagi	438	773	
	20.	6,455,892	9/24/02	Okuno et al.	257	328	
	21.	6,593,620	07/15/03	Hshieh et al.	257	335	
	22.	6,610,366	08/26/03	Lipkin et al.	427	378	
	23.	US200100558 52A1	12/01	Moise et al.	438	396	
<i>[Signature]</i>	24.	2002/0072247 A1	6/13/02	Lipkin et al.	438	767	

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FOREIGN PATENT DOCUMENTS								
		Document Number	Date	Country	Class	Subclass	Translation Yes   No	
	25	DE 10036208	2/14/02	Germany			Abstract	
	26	DE 198 09 554	9/10/98	Germany			Abstract	
	27	DE 19900171	12/26/00	Germany			Abstract	
	28	JP 03157974	7/5/91	Japan			Abstract	
	29	JP 08264766	10/11/96	Japan			Abstract	
	30	JP 09205202	8/5/97	Japan			Abstract	
	31	JP 11191559	7/13/99	Japan			Abstract	
	32	JP 11238742	8/31/99	Japan			Abstract	
	33	JP 11261061	9/24/99	Japan			Abstract	
	34	JP 11266017	9/28/99	Japan			Abstract	
	35	JP 11274487	10/8/99	Japan			Abstract	
	36	JP 2000049167	2/18/00	Japan			Abstract	
	37	JP 2000082812	3/21/00	Japan			Abstract	
	38	JP 2000106371	4/11/01	Japan			Abstract	
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	OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
		40.	A.K. Agarwal, J.B. Casady, L.B. Rowland, W.F. Valek, and C.D. Brandt, "1400 V 4H-SiC Power MOSFET's," <i>Materials Science Forum</i> Vols. 264-268, pp.989-992, 1998.					
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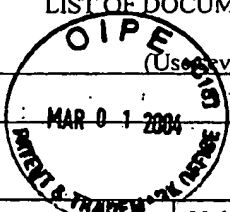
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46.	Chang et al. "Observation of a Non-stoichiometric Layer at the Silicon Dioxide--Silicon Carbide Interface: Effect of Oxidation Temperature and Post-Oxidation Processing Conditions," <i>Mat. Res. Soc. Symp. Proc.</i> Vol. 640, 2001.		
47.	Cho et al. "Improvement of charge trapping by hydrogen post-oxidation annealing in gate oxide of 4H-SiC methel-oxide-semiconductor capacitors," <i>Applied Physics Letters</i> . Vol. 77, No. 8, pp. 1215-7.		
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51.	Das, Mrinal K. Graduate thesis entitled, <i>Fundamental Studies of the Silicon Carbide MOS Structure</i> . Purdue University.		
52.	De Mao et al., "Thermal Oxidation of SiC in N <sub>2</sub> O", <i>J. Electrochem. Soc.</i> , Vol. 141, 1994, pp. L150-L152.		
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55.	G.Y. Chung, C.C. Tin, J.R. Williams, K. McDonald, M. Di Ventra, S.T. Pantelides, L.C. Feldman, and R.A. Weller, "Effect of nitric oxide annealing on the interface trap densities near the band edges in 4H," <i>Applied Physics Letters</i> , Vol. 76, No. 13, pp.1713-1715, March 2000.		
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* 60.	J.N. Shenoy, J.A. Cooper and M.R. Meelock, "High-Voltage Double-Implanted Power MOSFETs in 6H-SiC," <i>IEEE Electron Device Letters</i> , Vol. 18, No. 3, pp.93-95, March 1997		
61.	Jamet, et al. "Physical properties of N <sub>2</sub> O and NO-nitrided gate oxides grown on 4H SiC," <i>Applied Physics Letters</i> . Vol. 79, No.3, July 16, 2001, pp. 323-5.		
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Vol. 20, No. 12, pp. 624-626, December 1999.			
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66.	Lai et al. "Interface Properties of N <sub>2</sub> O-Annealed NH <sub>3</sub> -Treated 6H-SiC MOS Capacitor," <i>Electron Devices Meeting</i> , June 26, 1999, pp. 46-9.		
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75.	Pantelides et al. "Atomic-Scale Engineering of the SiC-SiO <sub>2</sub> Interface," <i>Materials Science Forum</i> . (2000) Vols. 338-342, pp. 1133-1136.		
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89.	Williams et al., "Passivation of the 4-H SiC/SiO <sub>2</sub> Interface with Nitric Oxide", <i>Materials Science Forum</i> , Vols. 389-393, 2002, pp. 967-972.		
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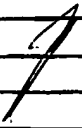

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		Document Number	Date	Country	Class	Subclass	Translation Yes   No
	2	WO99/63591	12/9/99	PCT			
<b>OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)</b>							
	3	International Search Report for PCT/US02/09393 dated 10/15/03.					
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	1	5,587,870	12/24/96	Anderson et al.	361	317		
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	2	Wang et al. "High Temperature Characteristics of High-Quality SiC MIS Capacitors with O/N/O Gate Dielectric." <i>IEEE Transactions on Electron Devices</i> . Vol. 47, No. 2, February 2000.						
	3	Invitation to Pay Additional Fees for PCT/US02/09393 dated 7/1/03.						

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